



NPN SILICON TRANSISTOR

NE856M03

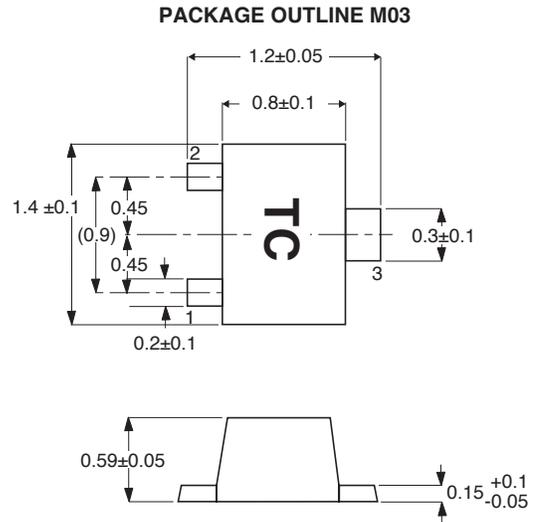
FEATURES

- **NEW M03 PACKAGE:**
 - Smallest transistor outline package available
 - Low profile/0.59 mm package height
 - Flat lead style for better RF performance
- **LOW NOISE FIGURE:**
NF = 1.4 dB at 1 GHz
- **HIGH COLLECTOR CURRENT:**
I_CMAX = 100 mA

DESCRIPTION

NEC's NE856M03 transistor is designed for low cost amplifier and oscillator applications. Low noise figure, high gain and high current capability equate to wide dynamic range and excellent linearity. NEC's new low profile/flat lead style "M03" package is ideal for today's portable wireless applications. The NE856 is also available in chip, Micro-x, and eight different low cost plastic surface mount package styles.

OUTLINE DIMENSIONS (Units in mm)



PIN CONNECTIONS

1. Emitter
2. Base
3. Collector

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

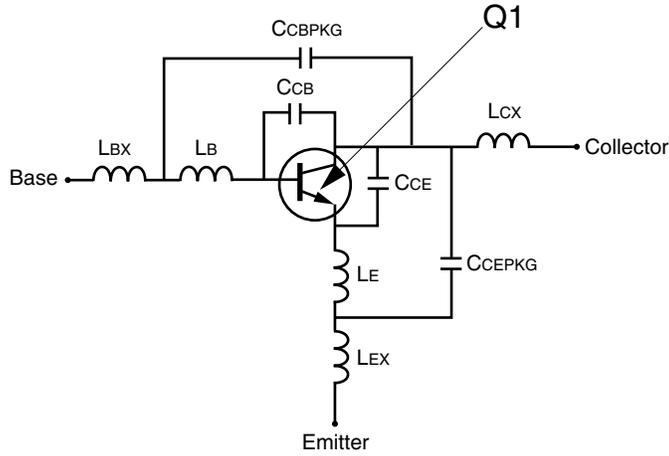
PART NUMBER EIAJ ¹ REGISTERED NUMBER PACKAGE OUTLINE		NE856M03 2SC5432 M03			
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
f _T	Gain Bandwidth at V _{CE} = 3 V, I _C = 7 mA, f = 1 GHz	GHz	3.0	4.5	
NF	Noise Figure at V _{CE} = 3 V, I _C = 7 mA, f = 1 GHz	dB		1.4	2.5
S _{21E} ²	Insertion Power Gain at V _{CE} = 3 V, I _C = 7 mA, f = 1 GHz	dB	7.0	10.0	
h _{FE} ²	Forward Current Gain at V _{CE} = 3 V, I _C = 7 mA		80		145
I _{CBO}	Collector Cutoff Current at V _{CB} = 10 V, I _E = 0	μA			1.0
I _{EBO}	Emitter Cutoff Current at V _{EB} = 1 V, I _C = 0	μA			1.0
C _{RE} ³	Feedback Capacitance at V _{CB} = 3 V, I _E = 0, f = 1 MHz	pF		0.7	1.5

Notes:

1. Electronic Industrial Association of Japan.
2. Pulsed measurement, pulse width ≤ 350 μs, duty cycle ≤ 2 %.
3. Capacitance is measured with emitter and case connected to the guard terminal at the bridge.

NONLINEAR MODEL

SCHEMATIC



BJT NONLINEAR MODEL PARAMETERS (1)

Parameters	Q1	Parameters	Q1
IS	9.2e-16	MJC	0.55
BF	110.3	XCJC	0.3
NF	1.01	CJS	0
VAF	18	VJS	0.75
IKF	1	MJS	0
ISE	4.89e-9	FC	0.5
NE	4.37	TF	4e-12
BR	10.08	XTF	30
NR	1.0	VTF	0.69
VAR	8	ITF	0.06
IKR	0.03	PTF	0
ISC	3.32e-11	TR	1e-9
NC	3.95	EG	1.11
RE	0.33	XTB	0
RB	1.26	XTI	3
RBM	2	KF	1.56e-18
IRB	0.05	AF	1.49
RC	6.63		
CJE	2.8e-12		
VJE	1.3		
MJE	0.5		
CJC	1.1e-12		
VJC	0.7		

UNITS

Parameter	Units
time	seconds
capacitance	farads
inductance	henries
resistance	ohms
voltage	volts
current	amps

ADDITIONAL PARAMETERS

Parameters	856M03
CcB	0.087e-12
CcE	0.16e-12
Lb	0.5e-9
Le	0.6e-9
CcBPKG	0.08e-12
CcEPKG	0.08e-12
LbX	0.12e-9
LcX	0.10e-9
Lx	0.12e-9

MODEL RANGE

Frequency: 0.1 to 4.0 GHz
 Bias: VCE = 0.5 V to 10 V, Ic = 0.5 mA to 10 mA
 Date: 11/98

(1) Gummel-Poon Model

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{CBO}	Collector to Base Voltage	V	20
V _{CEO}	Collector to Emitter Voltage	V	12
V _{EBO}	Emitter to Base Voltage	V	3
I _C	Collector Current	mA	100
P _T	Total Power Dissipation	mW	125
T _J	Junction Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to +150

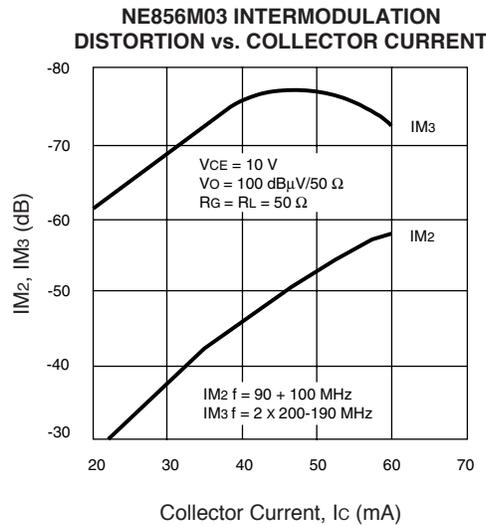
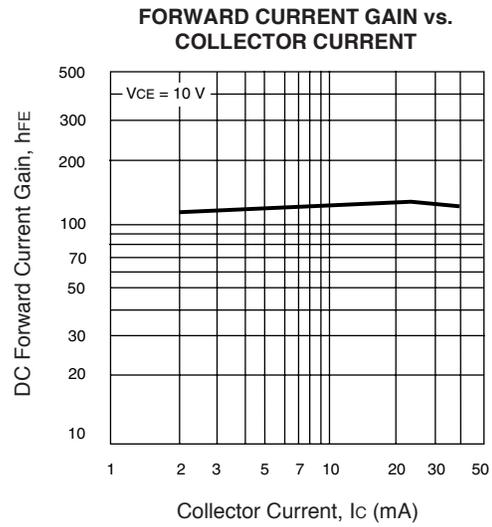
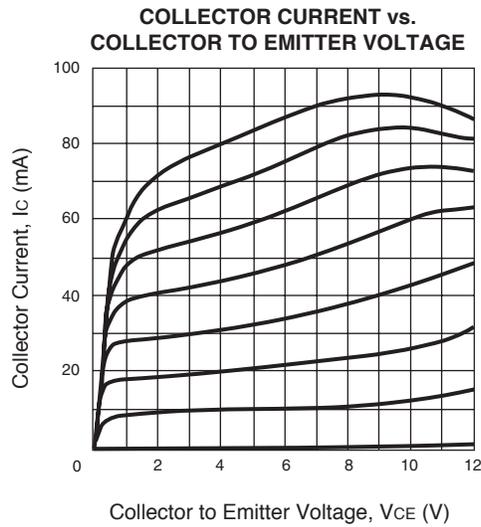
Note:

1. Operation in excess of any one of these parameters may result in permanent damage.

ORDERING INFORMATION

PART NUMBER	QUANTITY
NE856M03-A	
NE856M03-T1-A	

TYPICAL PERFORMANCE CURVES (T_A = 25°C)



Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL’s understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
		-A	-AZ
Lead (Pb)	< 1000 PPM	Not Detected	(*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
PBB	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

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